Lattice Semiconductor Corporation - <u>ICE40LP384-CM36 Datasheet</u>



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Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Detans	
Product Status	Active
Number of LABs/CLBs	48
Number of Logic Elements/Cells	384
Total RAM Bits	-
Number of I/O	25
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	36-VFBGA
Supplier Device Package	36-UCBGA (2.5x2.5)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/ice40lp384-cm36

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iCE40 LP/HX Family Data Sheet Introduction

March 2017

Features

- Flexible Logic Architecture
 - Five devices with 384 to 7,680 LUT4s and 10 to 206 I/Os
- Ultra Low Power Devices
 - Advanced 40 nm low power process
 - As low as 21 µA standby power
 - Programmable low swing differential I/Os

Embedded and Distributed Memory

- Up to 128 kbits sysMEM[™] Embedded Block RAM
- Pre-Engineered Source Synchronous I/O
- DDR registers in I/O cells
- High Current LED Drivers
 - Three High Current Drivers used for three different LEDs or one RGB LED
- High Performance, Flexible I/O Buffer
 - Programmable sysIO[™] buffer supports wide range of interfaces:
 - LVCMOS 3.3/2.5/1.8
 - LVDS25E, subLVDS

- Schmitt trigger inputs, to 200 mV typical hysteresis
- Programmable pull-up mode
- Flexible On-Chip Clocking
 - · Eight low-skew global clock resources
 - Up to two analog PLLs per device
- Flexible Device Configuration
 - SRAM is configured through:
 - Standard SPI Interface
 - Internal Nonvolatile Configuration Memory (NVCM)
- Broad Range of Package Options
 - WLCSP, QFN, VQFP, TQFP, ucBGA, caBGA, and csBGA package options
 - Small footprint package options — As small as 1.40 mm x 1.48 mm
 - Advanced halogen-free packaging

Part Number		LP384	LP640	LP1K	LP4K	LP8K	HX1K	HX4K	HX8K
Logic Cells (LUT + Flip-Flop))	384	640	1,280	3,520	7,680	1,280	3,520	7,680
RAM4K Memory Blocks		0	8	16	20	32	16	20	32
RAM4K RAM bits		0	32K	64K	80K	128K	64K	80K	128K
Phase-Locked Loops (PLLs)		0	0	1 ¹	2 ²	2 ²	1 ¹	2	2
Maximum Programmable I/C	Pins	63	25	95	167	178	95	95	206
Maximum Differential Input F	Pairs	8	3	12	20	23	11	12	26
High Current LED Drivers		0	3	3	0	0	0	0	0
Package	Code		•	Programn	hable I/O:	Max Inputs	(LVDS25)		
16 WLCSP (1.40 mm x 1.48 mm, 0.35 mm)	SWG16		10(0) ¹	10(0) ¹					
32 QFN (5 mm x 5 mm, 0.5 mm)	SG32	21(3)							
36 ucBGA (2.5 mm x 2.5 mm, 0.4 mm)	CM36	25(3)		25(3) ¹					
49 ucBGA (3 mm x 3 mm, 0.4 mm)	CM49	37(6)		35(5) ¹					
81 ucBGA (4 mm x 4 mm, 0.4 mm)	CM81			63(8)	63(9) ²	63(9) ²			
81 csBGA (5 mm x 5 mm, 0.5 mm)	CB81			62(9) ¹					

Table 1-1. iCE40 Family Selection Guide

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Data Sheet DS1040



Table 2-3. PLL Signal Descriptions

Signal Name	Direction	Description
REFERENCECLK	Input	Input reference clock
BYPASS	Input	When FEEDBACK_PATH is set to SIMPLE, the BYPASS control selects which clock sig- nal connects to the PLLOUT output.
DTFASS	mput	0 = PLL generated signal 1 = REFERENCECLK
EXTFEEDBACK	Input	External feedback input to PLL. Enabled when the FEEDBACK_PATH attribute is set to EXTERNAL.
DYNAMICDELAY[3:0]	Input	Fine delay adjustment control inputs. Enabled when DELAY_ADJUSTMENT_MODE is set to DYNAMIC.
LATCHINPUTVALUE	Input	When enabled, forces the PLL into low-power mode; PLL output is held static at the last input clock value. Set ENABLE ICEGATE_PORTA and PORTB to '1' to enable.
PLLOUTGLOBAL	Output	Output from the Phase-Locked Loop (PLL). Drives a global clock network on the FPGA. The port has optimal connections to global clock buffers GBUF4 and GBUF5.
PLLOUTCORE	Output	Output clock generated by the PLL, drives regular FPGA routing. The frequency gener- ated on this output is the same as the frequency of the clock signal generated on the PLLOUTLGOBAL port.
LOCK	Output	When High, indicates that the PLL output is phase aligned or locked to the input reference clock.
RESET	Input	Active low reset.

sysMEM Embedded Block RAM Memory

Larger iCE40 device includes multiple high-speed synchronous sysMEM Embedded Block RAMs (EBRs), each 4 kbit in size. This memory can be used for a wide variety of purposes including data buffering, and FIFO.

sysMEM Memory Block

The sysMEM block can implement single port, pseudo dual port, or FIFO memories with programmable logic resources. Each block can be used in a variety of depths and widths as shown in Table 2-4.

Block RAM Configuration	Block RAM Configuration and Size	WADDR Port Size (Bits)	WDATA Port Size (Bits)	RADDR Port Size (Bits)	RDATA Port Size (Bits)	MASK Port Size (Bits)
SB_RAM256x16 SB_RAM256x16NR SB_RAM256x16NW SB_RAM256x16NRNW	256x16 (4K)	8 [7:0]	16 [15:0]	8 [7:0]	16 [15:0]	16 [15:0]
SB_RAM512x8 SB_RAM512x8NR SB_RAM512x8NW SB_RAM512x8NRNW	512x8 (4K)	9 [8:0]	8 [7:0]	9 [8:0]	8 [7:0]	No Mask Port
SB_RAM1024x4 SB_RAM1024x4NR SB_RAM1024x4NW SB_RAM1024x4NRNW	1024x4 (4K)	10 [9:0]	4 [3:0]	10 [9:0]	4 [3:0]	No Mask Port
SB_RAM2048x2 SB_RAM2048x2NR SB_RAM2048x2NW SB_RAM2048x2NRNW	2048x2 (4K)	11 [10:0]	2 [1:0]	11 [10:0]	2 [1:0]	No Mask Port

Table 2-4. sysMEM Block Configurations¹

1. For iCE40 EBR primitives with a negative-edged Read or Write clock, the base primitive name is appended with a 'N' and a 'R' or 'W' depending on the clock that is affected.



RAM Initialization and ROM Operation

If desired, the contents of the RAM can be pre-loaded during device configuration.

By preloading the RAM block during the chip configuration cycle and disabling the write controls, the sysMEM block can also be utilized as a ROM.

Note the sysMEM Embedded Block RAM Memory address 0 cannot be initialized.

Memory Cascading

Larger and deeper blocks of RAM can be created using multiple EBR sysMEM Blocks.

RAM4k Block

Figure 2-4 shows the 256x16 memory configurations and their input/output names. In all the sysMEM RAM modes, the input data and addresses for the ports are registered at the input of the memory array.

Figure 2-4. sysMEM Memory Primitives

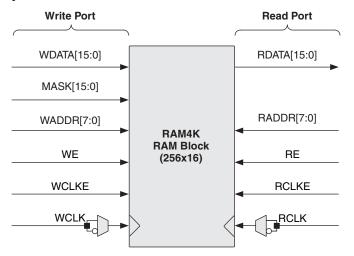


Table 2-5. EBR Signal Descriptions

Signal Name	Direction	Description
WDATA[15:0]	Input	Write Data input.
MASK[15:0]	Input	Masks write operations for individual data bit-lines. 0 = write bit; 1 = don't write bit
WADDR[7:0]	Input	Write Address input. Selects one of 256 possible RAM locations.
WE	Input	Write Enable input.
WCLKE	Input	Write Clock Enable input.
WCLK	Input	Write Clock input. Default rising-edge, but with falling-edge option.
RDATA[15:0]	Output	Read Data output.
RADDR[7:0]	Input	Read Address input. Selects one of 256 possible RAM locations.
RE	Input	Read Enable input.
RCLKE	Input	Read Clock Enable input.
RCLK	Input	Read Clock input. Default rising-edge, but with falling-edge option.

For further information on the sysMEM EBR block, please refer to TN1250, Memory Usage Guide for iCE40 Devices.



Power On Reset

iCE40 devices have power-on reset circuitry to monitor V_{CC} , V_{CCIO_2} , V_{PP_2V5} , and V_{CC_SPI} voltage levels during power-up and operation. At power-up, the POR circuitry monitors V_{CC} , V_{CCIO_2} , V_{PP_2V5} , and V_{CC_SPI} (controls configuration) voltage levels. It then triggers download from the on-chip NVCM or external Flash memory after reaching the power-up levels specified in the Power-On-Reset Voltage table in the DC and Switching Characteristics section of this data sheet. Before and during configuration, the I/Os are held in tri-state. I/Os are released to user functionality once the device has finished configuration.

Programming and Configuration

This section describes the programming and configuration of the iCE40 family.

Device Programming

The NVCM memory can be programmed through the SPI port.

Device Configuration

There are various ways to configure the Configuration RAM (CRAM) including:

- 1. Internal NVCM Download
- 2. From a SPI Flash (Master SPI mode)
- 3. System microprocessor to drive a Serial Slave SPI port (SSPI mode)

The image to configure the CRAM can be selected by the user on power up (Cold Boot) or once powered up (Warm Boot).

For more details on programming and configuration, see TN1248, iCE40 Programming and Configuration Usage Guide.

Power Saving Options

iCE40 devices are available in two options for maximum flexibility: LP and HX devices. The LP devices have ultra low static and dynamic power consumption. HX devices are designed to provide high performance. Both the LP and the HX devices operate at 1.2 V V_{CC} .

iCE40 devices feature iCEGate and PLL low power mode to allow users to meet the static and dynamic power requirements of their applications. While these features are available in both device types, these features are mainly intended for use with iCE40 LP devices to manage power consumption.

Table 2-9. iCE40 Power Saving Features Description

Device Subsystem	Feature Description
	When LATCHINPUTVALUE is enabled, forces the PLL into low-power mode; PLL output held static at last input clock value.
	To save power, the optional iCEgate latch can selectively freeze the state of individual, non-regis- tered inputs within an I/O bank. Registered inputs are effectively frozen by their associated clock or clock-enable control.



DC Electrical Characteristics

Over Recommended Operating Conditions

Symbol	Parameter	Condition	Min.	Тур.	Max.	Units
I _{IL,} I _{IH} ^{1, 3, 4, 5, 6, 7}	Input or I/O Leakage	$0V < V_{IN} < V_{CCIO} + 0.2 V$	—	_	+/—10	μA
C ₁ ^{6, 7}	I/O Capacitance ²	$V_{CCIO} = 3.3 V, 2.5 V, 1.8 V$ $V_{CC} = Typ., V_{IO} = 0 to V_{CCIO} + 0.2 V$	_	6	_	pf
C ₂ ^{6, 7}	Global Input Buffer Capacitance ²	$V_{CCIO} = 3.3 V, 2.5 V, 1.8 V$ $V_{CC} = Typ., V_{IO} = 0 to V_{CCIO} + 0.2 V$	_	6	_	pf
V _{HYST}	Input Hysteresis	V _{CCIO} = 1.8 V, 2.5 V, 3.3 V	—	200		mV
I _{PU} ^{6, 7}	Internal PIO Pull-up	$V_{CCIO} = 1.8 \text{ V}, 0 = < V_{IN} < = 0.65 \text{ V}_{CCIO}$	-3		-31	μΑ
	Current	$V_{CCIO} = 2.5 \text{ V}, 0 = < V_{IN} < = 0.65 \text{ V}_{CCIO}$	-8	—	-72	μA
		$V_{CCIO} = 3.3 \text{ V}, 0 = < V_{IN} < = 0.65 \text{ V}_{CCIO}$	-11	—	-128	μA

1. Input or I/O leakage current is measured with the pin configured as an input or as an I/O with the output driver tri-stated. It is not measured with the output driver active. Internal pull-up resistors are disabled.

2. T_J 25°C, f = 1.0 MHz.

3. Please refer to VIL and VIH in the sysIO Single-Ended DC Electrical Characteristics table of this document.

4. Only applies to IOs in the SPI bank following configuration.

5. Some products are clamped to a diode when V_{IN} is larger than $V_{\text{CCIO}}.$

6. High current IOs has three sysIO buffers connected together.

7. The iCE40LP640 and iCE40LP1K SWG16 package has CDONE and a sysIO buffer are connected together.

Static Supply Current – LP Devices^{1, 2, 3, 4}

Symbol	Parameter	Device	Typ. V _{CC} ⁴	Units
		iCE40LP384	21	μA
		iCE40LP640	100	μA
I _{CC}	Core Power Supply	iCE40LP1K	100	μA
		iCE40LP4K	250	μA
		iCE40LP8K	250	μA
I _{CCPLL} ^{5, 6}	PLL Power Supply	All devices	0.5	μA
I _{PP_2V5}	NVCM Power Supply	All devices	1.0	μA
ICCIO, ICC_SPI	Bank Power Supply⁴ V _{CCIO} = 2.5 V	All devices	3.5	μΑ

1. Assumes blank pattern with the following characteristics: all outputs are tri-stated, all inputs are configured as LVCMOS and held at V_{CCIO} or GND, on-chip PLL is off. For more detail with your specific design, use the Power Calculator tool. Power specified with master SPI configuration mode. Other modes may be up to 25% higher.

2. Frequency = 0 MHz.

3. $T_J = 25$ °C, power supplies at nominal voltage.

4. Does not include pull-up.

5. No PLL available on the iCE40LP384 and iCE40LP640 device.

6. V_{CCPLL} is tied to V_{CC} internally in packages without PLLs pins.



Programming NVCM Supply Current – HX Devices^{1, 2, 3, 4}

Symbol	Parameter	Device	Typ. V _{CC} ⁵	Units
		iCE40HX1K	278	μΑ
I _{CC}	Core Power Supply	iCE40HX4K	1174	μΑ
		iCE40HX8K	1174	μA
I _{CCPLL} ⁶	PLL Power Supply	All devices	0.5	μA
I _{PP_2V5}	NVCM Power Supply	All devices	2.5	mA
I _{CCIO⁷, I_{CC_SPI}}	Bank Power Supply⁵	All devices	3.5	mA

1. Assumes all inputs are held at V_{CCIO} or GND and all outputs are tri-stated.

2. Typical user pattern.

3. SPI programming is at 8 MHz.

4. $T_J = 25$ °C, power supplies at nominal voltage.

5. Per bank. V_{CCIO} = 2.5 V. Does not include pull-up.

6. V_{CCPLL} is tied to V_{CC} internally in packages without PLLs pins.

7. V_{PP FAST}, used only for fast production programming, must be left floating or unconnected in applications.

Peak Startup Supply Current – LP Devices

Symbol	Parameter	Device	Max	Units
		iCE40LP384	7.7	mA
		iCELP640	6.4	mA
I _{CCPEAK}	Core Power Supply	iCE40LP1K	6.4	mA
		iCE40LP4K	15.7	mA
		iCE40LP8K	15.7	mA
		iCE40LP1K	1.5	mA
1, 2, 4	PLL Power Supply	iCELP640	1.5	mA
CCPLLPEAK		iCE40LP4K	8.0	mA
		iCE40LP1K iCE40LP4K iCE40LP8K iCE40LP1K iCE40LP1K iCE40LP4K iCE40LP4K iCE40LP4K iCE40LP4K iCE40LP4K iCE40LP8K iCE40LP384 iCE40LP1K iCE40LP1K iCE40LP1K iCE40LP4K iCE40LP4K iCE40LP4K iCE40LP384 iCE40LP384 iCE40LP384 iCE40LP384 iCE40LP384 iCE40LP1K iCE40LP384 iCE40LP384 iCE40LP384 iCE40LP384 iCE40LP384 iCE40LP384 iCELP640	8.0	mA
		iCE40LP384	3.0	mA
		iCELP640	7.7	mA
I _{PP_2V5PEAK}	NVCM Power Supply	iCE40LP1K	7.7	mA
		iCE40LP4K	4.2	mA
		iCE40LP8K	4.2	mA
		iCE40LP384	5.7	mA
IPP_FASTPEAK ³	NVCM Programming Supply	iCELP640	8.1	mA
		iCE40LP1K	8.1	mA
		iCE40LP384	8.4	mA
		iCELP640	3.3	mA
I _{CCIOPEAK} ⁵ , I _{CC_SPIPEAK}	Bank Power Supply	iCE40LP1K	3.3	mA
		iCE40LP4K	8.2	mA
P_FASTPEAK ³		iCE40LP8K	8.2	mA

1. No PLL available on the iCE40LP384 and iCE40LP640 device.

2. V_{CCPLL} is tied to V_{CC} internally in packages without PLLs pins.

3. V_{PP_FAST}, used only for fast production programming, must be left floating or unconnected in applications, except CM36 and CM49 packages MUST have the V_{PP_FAST} ball connected to V_{CCIO_0} ball externally.

4. While no PLL is available in the iCE40-LP640 the I_{CCPLLPEAK} is additive to I_{CCPEAK}.

5. iCE40LP384 requires V_{CC} to be greater than 0.7 V when V_{CCIO} and V_{CC_SPI} are above GND.



Peak Startup Supply Current – HX Devices

Symbol	Parameter	Device	Max	Units
		iCE40HX1K	6.9	mA
ICCPEAK	Core Power Supply	iCE40HX4K	22.3	mA
		iCE40HX8K	22.3	mA
		iCE40HX1K	1.8	mA
I _{CCPLLPEAK} ¹	PLL Power Supply	iCE40HX4K	6.4	mA
		iCE40HX8K	6.4	mA
		iCE40HX1K	2.8	mA
I _{PP_2V5PEAK}	NVCM Power Supply	iCE40HX4K	4.1	mA
		iCE40HX8K	4.1	mA
		iCE40HX1K	6.8	mA
ICCIOPEAK, ICC_SPIPEAK	Bank Power Supply	iCE40HX4K	6.8	mA
		iCE40HX8K	6.8	mA

1. V_{CCPLL} is tied to V_{CC} internally in packages without PLLs pins.

sysIO Recommended Operating Conditions

	V _{CCIO} (V)				
Standard	Min.	Тур.	Max.		
LVCMOS 3.3	3.14	3.3	3.46		
LVCMOS 2.5	2.37	2.5	2.62		
LVCMOS 1.8	1.71	1.8	1.89		
LVDS25E ^{1, 2}	2.37	2.5	2.62		
subLVDSE ^{1, 2}	1.71	1.8	1.89		

1. Inputs on-chip. Outputs are implemented with the addition of external resistors.

2. Does not apply to Configuration Bank V_{CC_SPI}.

sysIO Single-Ended DC Electrical Characteristics

Input/	V	IL		V _{IL}		V _{IH} ¹			1	
Output Standard	Min. (V)	Max. (V)	Min. (V)	Max. (V)	V _{OL} Max. (V)	V _{OH} Min. (V)	I _{OL} Max. (mA)	I _{OH} Max. (mA)		
LVCMOS 3.3	-0.3	0.8	2.0	V _{CCIO} + 0.2 V	0.4	$V_{CCIO} - 0.4$	8, 16 ² , 24 ²	-8, -16 ² , -24 ²		
EVOINOU 0.0	0.0	0.0	2.0	V CCIO + 0.2 V	0.2	$V_{CCIO} - 0.2$	0.1	-0.1		
LVCMOS 2.5	-0.3	0.7	1.7	V _{CCIO} + 0.2 V	0.4	$V_{CCIO} - 0.4$	6, 12 ² , 18 ²	-6, -12 ² , -18 ²		
2.0	0.0	0.7	1.7	V CCIO + 0.2 V	0.2	$V_{CCIO} - 0.2$	0.1	-0.1		
LVCMOS 1.8	-0.3	0.35V _{CCIO}	0.65V _{CCIO}		0.4	$V_{CCIO} - 0.4$	4, 8 ² , 12 ²	-4, -8 ² , -12 ²		
	-0.5	0.33 A CCIO	0.03 A CCIO	V _{CCIO} + 0.2 V	0.2	$V_{CCIO} - 0.2$	0.1	-0.1		

1. Some products are clamped to a diode when V_{IN} is larger than $V_{\text{CCIO.}}$

2. Only for High Drive LED outputs.



SubLVDS Emulation

The iCE40 family supports the differential subLVDS standard. The output standard is emulated using complementary LVCMOS outputs in conjunction with resistors across the driver outputs on all banks of the devices. The sub-LVDS input standard is supported by the LVDS25 differential input buffer. The scheme shown in Figure 3-2 is one possible solution for subLVDSE output standard implementation. Use LVDS25E mode with suggested resistors for subLVDSE operation. Resistor values in Figure 3-2 are industry standard values for 1% resistors.

Figure 3-2. subLVDSE

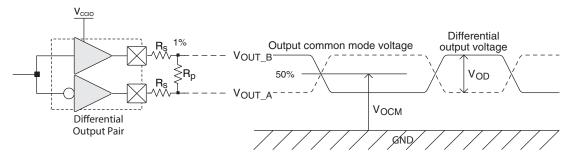


Table 3-2. subLVDSE DC Conditions

Parameter	Description	Тур.	Units
Z _{OUT}	Output impedance	20	Ohms
R _S	Driver series resistor	270	Ohms
R _P	Driver parallel resistor	120	Ohms
R _T	Receiver termination	100	Ohms
V _{OH}	Output high voltage	1.43	V
V _{OL}	Output low voltage	1.07	V
V _{OD}	Output differential voltage	0.35	V
V _{CM}	Output common mode voltage	0.9	V
Z _{BACK}	Back impedance	100.5	Ohms
I _{DC}	DC output current	2.8	mA

Over Recommended Operating Conditions



Derating Logic Timing

Logic timing provided in the following sections of the data sheet and the Lattice design tools are worst case numbers in the operating range. Actual delays may be much faster. Lattice design tools can provide logic timing numbers at a particular temperature and voltage.

Maximum sysIO Buffer Performance²

I/O Standard	Max. Speed	Units							
Inputs									
LVDS251	400	MHz							
subLVDS18 ¹	400	MHz							
LVCMOS33	250	MHz							
LVCMOS25	250	MHz							
LVCMOS18	250	MHz							
	Outputs								
LVDS25E	250	MHz							
subLVDS18E	155	MHz							
LVCMOS33	250	MHz							
LVCMOS25	250	MHz							
LVCMOS18	155	MHz							

1. Supported in Bank 3 only.

2. Measured with a toggling pattern

iCE40 Family Timing Adders

Over Recommended Commercial Operating Conditions - LP Devices^{1, 2, 3, 4, 5}

Buffer Type	Description	Timing	Units
Input Adjusters	I		
LVDS25	LVDS, $V_{CCIO} = 2.5 V$	-0.18	ns
subLVDS	subLVDS, V _{CCIO} = 1.8 V	0.82	ns
LVCMOS33	LVCMOS, V _{CCIO} = 3.3 V	0.18	ns
LVCMOS25	LVCMOS, V _{CCIO} = 2.5 V	0.00	ns
LVCMOS18	LVCMOS, V _{CCIO} = 1.8 V	0.19	ns
Output Adjusters			
LVDS25E	LVDS, Emulated, V _{CCIO} = 2.5 V	0.00	ns
subLVDSE	subLVDS, Emulated, V _{CCIO} = 1.8 V	1.32	ns
LVCMOS33	LVCMOS, V _{CCIO} = 3.3 V	-0.12	ns
LVCMOS25	LVCMOS, V _{CCIO} = 2.5 V	0.00	ns
LVCMOS18	LVCMOS, V _{CCIO} = 1.8 V	1.32	ns

1. Timing adders are relative to LVCMOS25 and characterized but not tested on every device.

2. LVCMOS timing measured with the load specified in Switching Test Condition table.

3. All other standards tested according to the appropriate specifications.

4. Commercial timing numbers are shown.

5. Not all I/O standards are supported for all banks. See the Architecture section of this data sheet for details.



Over Recommended Commercial Operating Conditions - HX Devices^{1, 2, 3, 4, 5}

Buffer Type	Description	Timing	Units
Input Adjusters	I		
LVDS25	LVDS, $V_{CCIO} = 2.5 V$	0.13	ns
subLVDS	subLVDS, V _{CCIO} = 1.8 V	1.03	ns
LVCMOS33	LVCMOS, V _{CCIO} = 3.3 V	0.16	ns
LVCMOS25	LVCMOS, V _{CCIO} = 2.5 V	0.00	ns
LVCMOS18	LVCMOS, V _{CCIO} = 1.8 V	0.23	ns
Output Adjusters	· · ·		
LVDS25E	LVDS, Emulated, V _{CCIO} = 2.5 V	0.00	ns
subLVDSE	subLVDS, Emulated, V _{CCIO} = 1.8 V	1.76	ns
LVCMOS33	LVCMOS, V _{CCIO} = 3.3 V	0.17	ns
LVCMOS25	LVCMOS, V _{CCIO} = 2.5 V	0.00	ns
LVCMOS18	LVCMOS, V _{CCIO} = 1.8 V	1.76	ns

1. Timing adders are relative to LVCMOS25 and characterized but not tested on every device.

2. LVCMOS timing measured with the load specified in Switching Test Condition table.

3. All other standards tested according to the appropriate specifications.

4. Commercial timing numbers are shown.

5. Not all I/O standards are supported for all banks. See the Architecture section of this data sheet for details.



iCE40 External Switching Characteristics – HX Devices ^{1, 2}

Over Recommended Operating Conditions

Parameter	Description	Device	Min.	Max.	Units
Clocks					
Primary Clocks					
f _{MAX_GBUF}	Frequency for Global Buffer Clock network	All iCE40HX devices	_	275	MHz
t _{W_GBUF}	Clock Pulse Width for Global Buffer	All iCE40HX devices	0.88	—	ns
		iCE40HX1K	—	727	ps
t _{SKEW_GBUF}	Global Buffer Clock Skew Within a Device	iCE40HX4K	—	300	ps
		iCE40HX8K	OHX devices 0.88 X1K 727 X4K 300 X8K 300 0 HX devices 7.30 0 HX devices 7.30 X1K 696 X4K 290 X1K 5.00 X4K 5.41 X8K 5.41 X1K 5.41 X1K -0.23 X4K -0.43 X4K -0.43 X4K 2.38 X4K 2.38 X4K 2.38 X4K - 2.51 X4K - 2.51 X4K - - X4K - - X4K - - X4K - - X4K - -	ps	
Pin-LUT-Pin Prop	agation Delay	•	I		1
t _{PD}	Best case propagation delay through one LUT-4	All iCE40 HX devices	_	7.30	ns
General I/O Pin P	arameters (Using Global Buffer Clock witho	ut PLL)		•	
		iCE40HX1K	—	696	ps
t _{SKEW_IO}	Data bus skew across a bank of IOs	iCE40HX4K	—	290	ps
		iCE40HX8K	—	290	ps
		iCE40HX1K	—	5.00	ns
co	Clock to Output - PIO Output Register	iCE40HX4K	—	5.41	ns
		iCE40HX8K	—		ns
		iCE40HX1K	-0.23	—	ns
t _{SU}	Clock to Data Setup - PIO Input Register	iCE40HX4K	-0.43	—	ns
		iCE40HX8K	-0.43	275 	ns
		iCE40HX1K	1.92	—	ns
t _H	Clock to Data Hold - PIO Input Register	iCE40HX4K	2.38	—	ns
		iCE40HX8K	2.38	275 	ns
General I/O Pin P	arameters (Using Global Buffer Clock with I	PLL) ³			
		iCE40HX1K	—	2.96	ns
t _{COPLL}	Clock to Output - PIO Output Register	iCE40HX4K	—	2.51	ns
		iCE40HX8K	—	2.51	ns
		iCE40HX1K	3.10	—	ns
t _{SUPLL}	Clock to Data Setup - PIO Input Register	iCE40HX4K	4.16	—	ns
		iCE40HX8K	4.16	—	ns
		iCE40HX1K	-0.60	—	ns
t _{HPLL}	Clock to Data Hold - PIO Input Register	iCE40HX4K	-0.53	—	ns
AAX_GBUF V_GBUF SKEW_GBUF SKEW_GBUF in-LUT-Pin Propa D General I/O Pin Pa SKEW_IO CO SU		iCE40HX8K	-0.53	—	ns

1. Exact performance may vary with device and design implementation. Commercial timing numbers are shown at 85 °C and 1.14 V. Other operating conditions, including industrial, can be extracted from the iCECube2 software.

2. General I/O timing numbers based on LVCMOS 2.5, 0pf load.

3. Supported on devices with a PLL.



SPI Master or NVCM Configuration Time^{1, 2}

Symbol	Parameter	Conditions	Тур.	Units
	iCE40LP384 - Low Frequency (Default)	25	ms	
		iCE40LP384 - Medium Frequency	15	ms
		iCE40LP384 - High Frequency	11	ms
		iCE40LP640 - Low Frequency (Default)	53	ms
		iCE40LP640 - Medium Frequency	25	ms
		iCE40LP640 - High Frequency	13	ms
		iCE40LP/HX1K - Low Frequency (Default)	53	ms
t _{CONFIG}	POR/CRESET_B to Device I/O Active	iCE40LP/HX1K - Medium Frequency	25	ms
		iCE40LP/HX1K - High Frequency	13	ms
		iCE40LP/HX4K - Low Frequency (Default)	230	ms
		iCE40LP/HX4K - Medium Frequency	110	ms
		iCE40LP/HX4K - High Frequency	70	ms
		iCE40LP/HX8K - Low Frequency (Default)	230	ms
		iCE40LP/HX8K - Medium Frequency	110	ms
		iCE40LP/HX8K - High Frequency	70	ms

1. Assumes sysMEM Block is initialized to an all zero pattern if they are used.

2. The NVCM download time is measured with a fast ramp rate starting from the maximum voltage of POR trip point.



sysCONFIG Port Timing Specifications¹ (Continued)

Symbol	Parameter		Min.	Тур.	Max.	Units
		iCE40LP384 - Low Frequency (Default)	600	_	—	us
		iCE40LP384 - Medium Frequency	600	_	—	us
		iCE40LP384 - High Frequency	600	_	—	us
		iCE40LP640, iCE40LP/HX1K - Low Frequency (Default)	800	_	_	us
		iCE40LP640, iCE40LP/HX1K - Medium Frequency	800	_	_	us
		iCE40LP640, iCE40LP/HX1K - High Frequency	800		_	us
	CRESET_B high to first MCLK	iCE40LP/HX1K-Low Frequency (Default)	800	_	—	us
^I MCLK	edge	iCE40LP/HX1K - Medium Frequency	800	_	—	us
		iCE40LP/HX1K - High Frequency	800	_	—	us
		iCE40LP/HX4K - Low Frequency (Default)	1200		—	us
		iCE40LP/HX4K - Medium Frequency	1200	_	—	us
		iCE40LP/HX4K - high frequency	1200	_	—	US
		iCE40LP/HX8K - Low Frequency (Default)	1200	_	—	us
		iCE40LP/HX8K - Medium Frequency	1200		—	us
		iCE40LP/HX8K - High Frequency	1200			us

Does not apply for NVCM.
 Supported only with 1.2 V V_{CC} and at 25 °C.
 Extended range f_{MAX} Write operations support up to 53 MHz only with 1.2 V V_{CC} and at 25 °C.



Switching Test Conditions

Figure 3-3 shows the output test load used for AC testing. The specific values for resistance, capacitance, voltage, and other test conditions are shown in Table 3-3.

Figure 3-3. Output Test Load, LVCMOS Standards

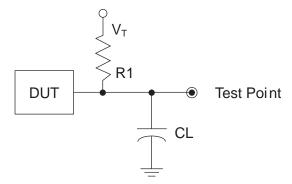


Table 3-3. Test Fixture Required Components, Non-Terminated Interfaces

Test Condition	R ₁	CL	Timing Reference	V _T
			LVCMOS 3.3 = 1.5 V	—
LVCMOS settings (L -> H, H -> L)	×	0 pF	LVCMOS 2.5 = $V_{CCIO}/2$	—
			LVCMOS 1.8 = $V_{CCIO}/2$	—
LVCMOS 3.3 (Z -> H)			1.5	V _{OL}
LVCMOS 3.3 (Z -> L)			1.5	V _{OH}
Other LVCMOS (Z -> H)	188	0 pF	V _{CCIO} /2	V _{OL}
Other LVCMOS (Z -> L)	100	0 pr	V _{CCIO} /2	V _{OH}
LVCMOS (H -> Z)			V _{OH} - 0.15	V _{OL}
LVCMOS (L -> Z)			V _{OL} - 0.15	V _{OH}

Note: Output test conditions for all other interfaces are determined by the respective standards.



iCE40 LP/HX Family Data Sheet Pinout Information

March 2017

Data Sheet DS1040

Signal Descriptions

Signal Name	I/O	Descriptions
General Purpose		
IO[Bank]_[Row/Column Number][A/B]	I/O	[Bank] indicates the bank of the device on which the pad is located. [Number] indicates IO number on the device.
IO[Bank]_[Row/Column Number][A/B]	I/O	[Bank] indicates the bank of the device on which the pad is located. [Number] indicates IO number on the device. [A/B] indicates the differential I/O. 'A' = negative input. 'B' = positive input.
HCIO[Bank]_[Number]	I/O	High Current IO. [Bank] indicates the bank of the device on which the pad is located. [Number] indicates IO number.
NC	—	No connect
GND	—	GND – Ground. Dedicated pins. It is recommended that all GNDs are tied together.
VCC	—	VCC – The power supply pins for core logic. Dedicated pins. It is recommended that all VCCs are tied to the same supply.
VCCIO_x	—	VCCIO – The power supply pins for I/O Bank x. Dedicated pins. All VCCIOs located in the same bank are tied to the same supply.
PLL and Global Functions (Used as u	ser-programmable I/O pins when not used for PLL or clock pins)
VCCPLLx	_	PLL VCC – Power. Dedicated pins. The PLL requires a separate power and ground that is quiet and stable to reduce the output clock jitter of the PLL.
GNDPLLx	_	PLL GND – Ground. Dedicated pins. The sysCLOCK PLL has the DC ground con- nection made on the FPGA, so the external PLL ground connection (GNDPLL) must NOT be connected to the board's ground.
GBINx	—	Global pads. Two per side.
Programming and Configur	ation	
CBSEL[0:1]	I/O	Dual function pins. I/Os when not used as CBSEL. Optional ColdBoot configuration SELect input, if ColdBoot mode is enabled.
CRESET_B	I	Configuration Reset, active Low. Dedicated input. No internal pull-up resistor. Either actively drive externally or connect a 10 KOhm pull-up resistor to VCCIO_2.
CDONE	I/O	Configuration Done. Includes a permanent weak pull-up resistor to VCCIO_2. If driv- ing external devices with CDONE output, an external pull-up resistor to VCCIO_2 may be required. Refer to the TN1248, iCE40 Programming and Configuration for more details. Following device configuration the iCE40LP640 and iCE40LP1K in the SWG16 package CDONE pin can be used as a user output.
VCC_SPI	—	SPI interface voltage supply input. Must have a valid voltage even if configuring from NVCM.
SPI_SCK	I/O	Input Configuration Clock for configuring an FPGA in Slave SPI mode. Output Configuration Clock for configuring an FPGA configuration modes.
SPI_SS_B	I/O	SPI Slave Select. Active Low. Includes an internal weak pull-up resistor to VCC_SPI during configuration. During configuration, the logic level sampled on this pin determines the configuration mode used by the iCE40 device. An input when sampled at the start of configuration. An input when in SPI Peripheral configuration mode (SPI_SS_B = Low). An output when in Master SPI Flash configuration mode.
SPI_SI	I/O	Slave SPI serial data input and master SPI serial data output
SPI_SO	I/O	Slave SPI serial data output and master SPI serial data input

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Pin Information Summary

	i	CE40LP38	84	iCE40LP640				iCE4	0LP1K			
	SG32	CM36 ²	CM49 ²	SWG16	SWG16	CM36 ^{1, 2}	CM49 ^{1, 2}	CM81	CB81	QN84	CM121	CB121
General Purpose I/O per Ban	k											
Bank 0	6	4	10	3	3	4	10	17	17	17	24	24
Bank 1	5	7	7	0	0	7	7	15	16	17	25	21
Bank 2	0	4	4	1	1	4	4	11	8	11	18	19
Bank 3	6	6	12	2	2	6	10	16	17	18	24	24
Configuration	4	4	4	4	4	4	4	4	4	4	4	4
Total General Purpose Single Ended I/O	21	25	37	10	10	25	35	63	62	67	95	92
High Current Outputs per Ba	ink		•									
Bank 0	0	0	0	3	3	0	0	0	0	0	0	0
Bank 1	0	0	0	0	0	0	0	0	0	0	0	0
Bank 2	0	0	0	0	0	0	0	0	0	0	0	0
Bank 3	0	0	0	0	0	0	0	0	0	0	0	0
Total Current Outputs	0	0	0	3	3	0	0	0	0	0	0	0
Differential Inputs per Bank				L						•		
Bank 0	0	0	0	0	0	0	0	0	0	0	0	0
Bank 1	0	0	0	0	0	0	0	0	0	0	0	0
Bank 2	0	0	0	0	0	0	0	0	0	0	0	0
Bank 3	3	3	6	1	1	3	5	8	9	7	12	12
Total Differential Inputs	3	3	6	1	1	3	5	8	9	7	12	12
Dedicated Inputs per Bank												
Bank 0	0	0	0	0	0	0	0	0	0	0	0	0
Bank 1	0	0	0	0	0	0	0	0	0	0	0	0
Bank 2	2	2	2	1	1	2	2	2	2	2	2	2
Bank 3	0	0	0	0	0	0	0	0	0	0	0	0
Configuration	0	0	0	0	0	0	0	0	0	0	0	0
Total Dedicated Inputs	2	2	2	1	1	2	2	2	2	2	2	2
Vccio Pins		1				1			1			
Bank 0	1	1	1	1	1	1	1	1	1	1	2	1
Bank 1	1	1	1	0	0	0	0	1	1	1	2	1
Bank 2	1	1	1	1	1	1	1	1	1	1	2	1
Bank 3	1	0	0	0	0	0	0	1	1	1	2	2
VCC	1	1	2	1	1	1	2	3	3	4	4	4
VCC_SPI	1	1	1	0	0	1	1	1	1	1	1	1
VPP_2V5	1	1	1	0	0	1	1	1	1	1	1	1
VPP_FAST ³	0	0	0	0	0	1	1	1	0	1	1	1
VCCPLL	0	0	0	0	0	0	1	1	0	0	1	1
GND	2	3	3	2	2	3	4	5	8	4	8	11
NC	0	0	0	0	0	0	0	0	0	0	0	3
Total Count of Bonded Pins	32	36	49	16	16	36	49	81	81	84	121	121

V_{CCIO2} and V_{CCIO1} are connected together.
 V_{CCIO2} and V_{CCIO3} are connected together.
 V_{PP_FAST}, used only for fast production programming, must be left floating or unconnected in applications, except CM36 and CM49 packages MUST have the V_{PP_FAST} ball connected to V_{CCIO_0} ball externally.



Pin Information Summary (Continued)

		iCE40LP4K			iCE40LP8K				
	CM81	CM121	CM225	CM81	CM121	CM225	VQ100	CB132	TQ144
General Purpose I/O per	r Bank								
Bank 0	17	23	46	17	23	46	19	24	23
Bank 1	15	21	42	15	21	42	19	25	25
Bank 2	9	19	40	9	19	40	12	20	20
Bank 3	18	26	46	18	26	46	18	22	24
Configuration	4	4	4	4	4	4	4	4	4
Total General Purpose Single Ended I/O	63	93	178	63	93	178	72	95	96
High Current Outputs p	er Bank	•	•			•			•
Bank 0	0	0	0	0	0	0	0	0	0
Bank 1	0	0	0	0	0	0	0	0	0
Bank 2	0	0	0	0	0	0	0	0	0
Bank 3	0	0	0	0	0	0	0	0	0
Total Differential Inputs	0	0	0	0	0	0	0	0	0
Differential Inputs per B	ank								
Bank 0	0	0	0	0	0	0	0	0	0
Bank 1	0	0	0	0	0	0	0	0	0
Bank 2	0	0	0	0	0	0	0	0	0
Bank 3	9	13	23	9	13	23	9	11	12
Total Differential Inputs	9	13	23	9	13	23	9	11	12
Dedicated Inputs per Ba	ank								
Bank 0	0	0	0	0	0	0	0	0	0
Bank 1	0	0	1	0	0	1	0	1	1
Bank 2	2	2	2	2	2	2	2	2	2
Bank 3	0	0	0	0	0	0	0	0	0
Configuration	0	0	0	0	0	0	0	0	0
Total Dedicated Inputs	2	2	3	2	2	3	2	3	3
Vccio Pins				•			•	•	
Bank 0	1	1	3	1	1	3	2	2	2
Bank 1	1	1	3	1	1	3	2	2	2
Bank 2	1	1	3	1	1	3	2	2	2
Bank 3	1	2	4	1	2	4	3	3	2
VCC	3	4	8	3	4	8	4	5	4
VCC_SPI	1	1	1	1	1	1	1	1	1
VPP_2V5	1	1	1	1	1	1	1	1	1
VPP_FAST ¹	1	1	1	1	1	1	1	1	1
VCCPLL	1	2	2	1	2	2	0	1	1
GND	5	12	18	5	12	18	10	14	10
NC	0	0	0	0	0	0	0	2	19
Total Count of Bonded Pins	81	121	225	81	121	225	100	132	144

1. V_{PP_FAST}, used only for fast production programming, must be left floating or unconnected in applications.



Pin Information Summary (Continued)

	iCE40HX4K			iCE40HX8K			
	BG121	CB132	TQ144	BG121	CB132	CM225	CT256
General Purpose I/O per Bank							
Bank 0	23	24	27	23	24	46	52
Bank 1	21	25	29	21	25	42	52
Bank 2	19	18	19	19	18	40	46
Bank 3	26	24	28	26	24	46	52
Configuration	4	4	4	4	4	4	4
Total General Purpose Single Ended I/O	93	95	107	93	95	178	206
High Current Outputs per Bank		•	•		•		
Bank 0	0	0	0	0	0	0	0
Bank 1	0	0	0	0	0	0	0
Bank 2	0	0	0	0	0	0	0
Bank 3	0	0	0	0	0	0	0
Total Differential Inputs	0	0	0	0	0	0	0
Differential Inputs per Bank	•	•			•	•	
Bank 0	0	0	0	0	0	0	0
Bank 1	0	0	0	0	0	0	0
Bank 2	0	0	0	0	0	0	0
Bank 3	13	12	14	13	12	23	26
Total Differential Inputs	13	12	14	13	12	23	26
Dedicated Inputs per Bank		•	•		•		
Bank 0	0	0	0	0	0	0	0
Bank 1	0	1	1	0	1	1	1
Bank 2	2	2	2	2	2	2	2
Bank 3	0	0	0	0	0	0	0
Configuration	0	0	0	0	0	0	0
Total Dedicated Inputs	2	3	3	2	3	3	3
Vccio Pins	•		•	•	•		•
Bank 0	1	2	2	1	2	3	4
Bank 1	1	2	2	1	2	3	4
Bank 2	1	2	2	1	2	3	4
Bank 3	2	3	2	2	3	4	4
VCC	4	5	4	4	5	8	6
VCC_SPI	1	1	1	1	1	1	1
VPP_2V5	1	1	1	1	1	1	1
VPP_FAST ¹	1	1	1	1	1	1	1
VCCPLL	2	2	2	2	2	2	2
GND	12	15	11	12	15	18	20
NC	0	0	6	0	0	0	0
Total Count of Bonded Pins	121	132	144	121	132	225	256

1. V_{PP_FAST}, used only for fast production programming, must be left floating or unconnected in applications.



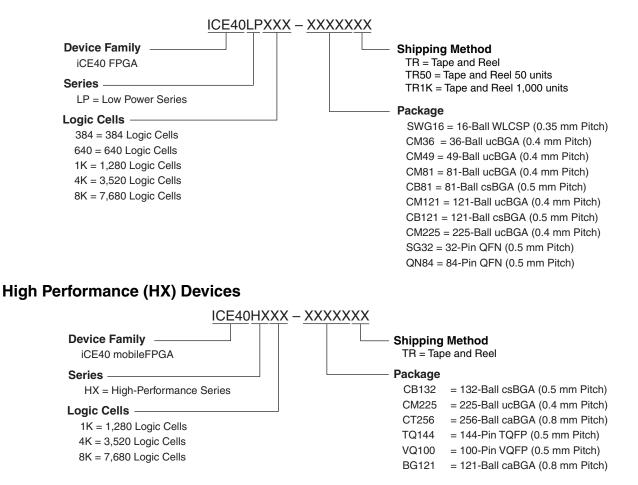
iCE40 LP/HX Family Data Sheet Ordering Information

March 2017

Data Sheet DS1040

iCE40 Part Number Description

Ultra Low Power (LP) Devices



All parts shipped in trays unless noted.

Ordering Information

iCE40 devices have top-side markings as shown below:



Note: Markings are abbreviated for small packages.

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Part Number	LUTs	Supply Voltage	Package	Leads	Temp.
ICE40LP8K-CM121TR1K	7680	1.2 V	Halogen-Free ucBGA	121	IND
ICE40LP8K-CM225	7680	1.2 V	Halogen-Free ucBGA	225	IND

High-Performance Industrial Grade Devices, Halogen Free (RoHS) Packaging

Part Number	LUTs	Supply Voltage	Package	Leads	Temp.
ICE40HX1K-CB132	1280	1.2 V	Halogen-Free csBGA	132	IND
ICE40HX1K-VQ100	1280	1.2 V	Halogen-Free VQFP	100	IND
ICE40HX1K-TQ144	1280	1.2 V	Halogen-Free TQFP	144	IND
ICE40HX4K-BG121	3520	1.2 V	Halogen-Free caBGA	121	IND
ICE40HX4K-BG121TR	3520	1.2 V	Halogen-Free caBGA	121	IND
ICE40HX4K-CB132	3520	1.2 V	Halogen-Free csBGA	132	IND
ICE40HX4K-TQ144	3520	1.2 V	Halogen-Free TQFP	144	IND
ICE40HX8K-BG121	7680	1.2 V	Halogen-Free caBGA	121	IND
ICE40HX8K-BG121TR	7680	1.2 V	Halogen-Free caBGA	121	IND
ICE40HX8K-CB132	7680	1.2 V	Halogen-Free csBGA	132	IND
ICE40HX8K-CM225	7680	1.2 V	Halogen-Free ucBGA	225	IND
ICE40HX8K-CT256	7680	1.2 V	Halogen-Free caBGA	256	IND